

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	-20	V
Gate-Source Voltage (Note 5)			V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = -4.5V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C T <sub>C</sub> = +25°C	I <sub>D</sub>	-14 -11 -54	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I <sub>DM</sub>	-80	A
Maximum Continuous Body Diode Forward Current (Note 6)			I <sub>S</sub>	-2.2	A
Avalanche Current (Note 8)			I <sub>AS</sub>	-15	A
Avalanche Energy (Note 8)			E <sub>AS</sub>	-113	mJ

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	2.4	W
	T <sub>C</sub> = +25°C		41	
Thermal Resistance, Junction to Ambient	(Note 5)	R <sub>θJA</sub>	52	°C/W
	(Note 6)		137	
Thermal Resistance, Junction to Case (Note 6)		R <sub>θJC</sub>	3.0	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1	μA	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.4	—	-1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	—	—	8	mΩ	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -12A
		—	—	9.8		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -10A
		—	—	13		V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -9.3A
		—	—	17		V <sub>GS</sub> = -1.5V, I <sub>D</sub> = -8.3A
Forward Transfer Admittance	Y <sub>fs</sub>	—	42	—	S	V <sub>DS</sub> = -5V, I <sub>D</sub> = -12A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C <sub>iss</sub>	—	6909	—	pF	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	635	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	563	—		
Gate Resistance	R <sub>G</sub>	—	2.5	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Q <sub>g</sub>	—	72	—	nC	V <sub>DD</sub> = -10V, I <sub>D</sub> = -12A
Total Gate Charge (V <sub>GS</sub> = -2.5V)	Q <sub>g</sub>	—	40	—		
Gate-Source Charge	Q <sub>gs</sub>	—	8.6	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	14.5	—		
Turn-On Delay Time	t <sub>D(on)</sub>	—	22	—	ns	V <sub>GS</sub> = -4.5V, V <sub>DD</sub> = -10V, R <sub>G</sub> = 6Ω, I <sub>D</sub> = -12A
Turn-On Rise Time	t <sub>r</sub>	—	33	—		
Turn-Off Delay Time	t <sub>D(off)</sub>	—	291	—		
Turn-Off Fall Time	t <sub>f</sub>	—	124	—		
BODY DIODE CHARACTERISTICS						
Diode Forward Voltage	V <sub>SD</sub>	—	-0.7	—	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -12A
		—	-0.7	—	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -2A
Reverse Recovery Time (Note 10)	t <sub>rr</sub>	—	25	—	ns	I <sub>F</sub> = -12A, di/dt = 100A/μs
Reverse Recovery Charge (Note 10)	Q <sub>rr</sub>	—	15	—	nC	I <sub>F</sub> = -12A, di/dt = 100A/μs

- Notes:
- AEC-Q101 V<sub>GS</sub> maximum is ±6.4V.
  - R<sub>θJA</sub> is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. R<sub>θJC</sub> is guaranteed by design while R<sub>θJA</sub> is determined by the user's board design.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - UIS in production with L = 1mH, T<sub>J</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

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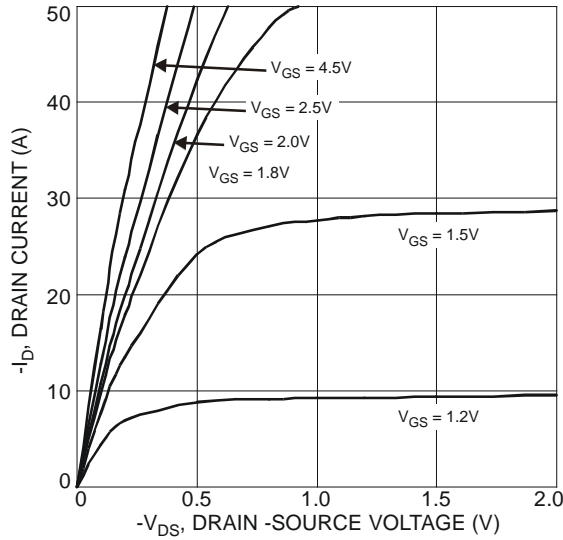


Fig. 1 Typical Output Characteristics

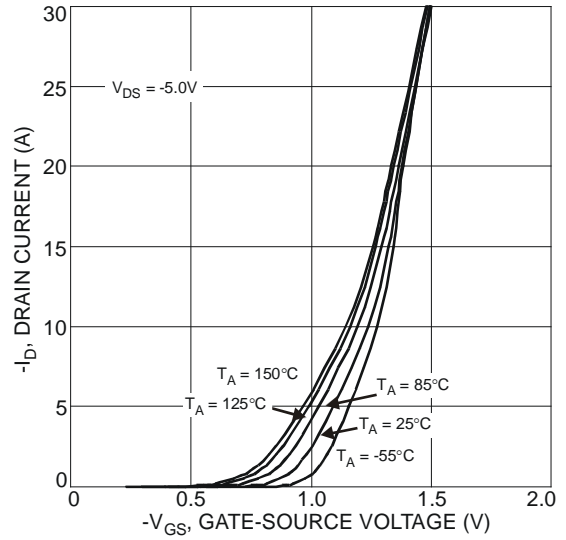


Fig. 2 Typical Transfer Characteristics

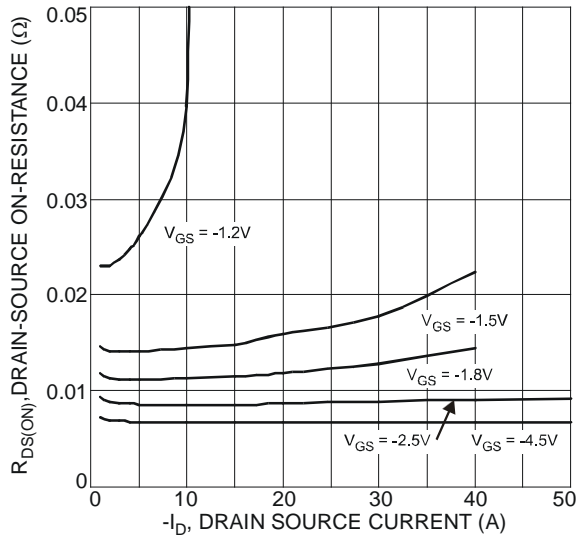


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

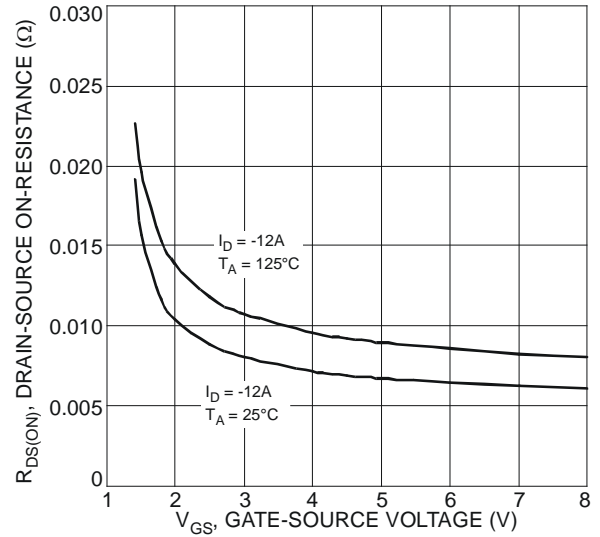


Fig. 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

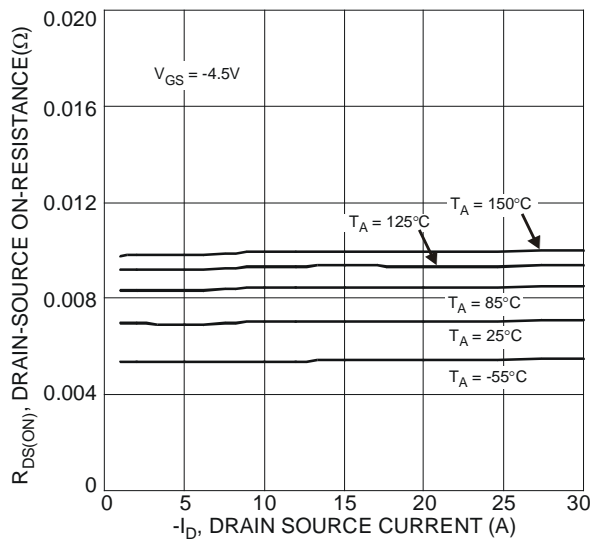


Fig. 5 Typical On-Resistance vs. Drain Current and Temperature

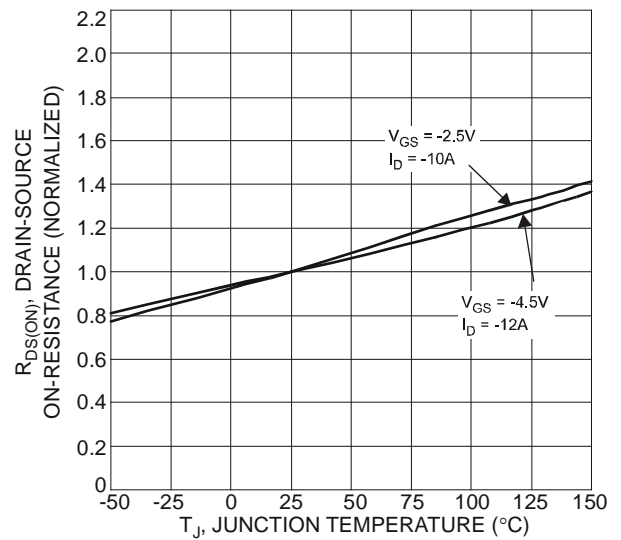


Fig. 6 On-Resistance Variation with Temperature

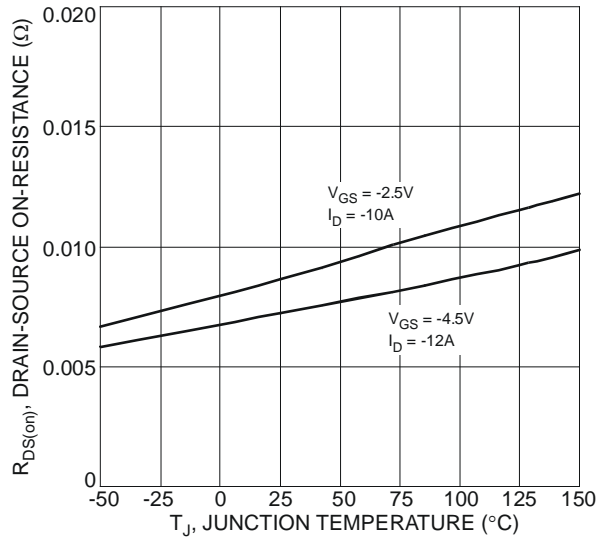


Fig. 7 On-Resistance Variation with Temperature

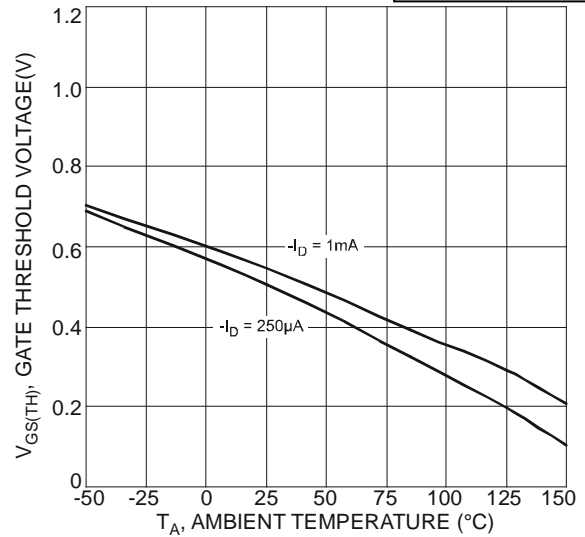


Fig. 8 Gate Threshold Variation vs. Ambient Temperature

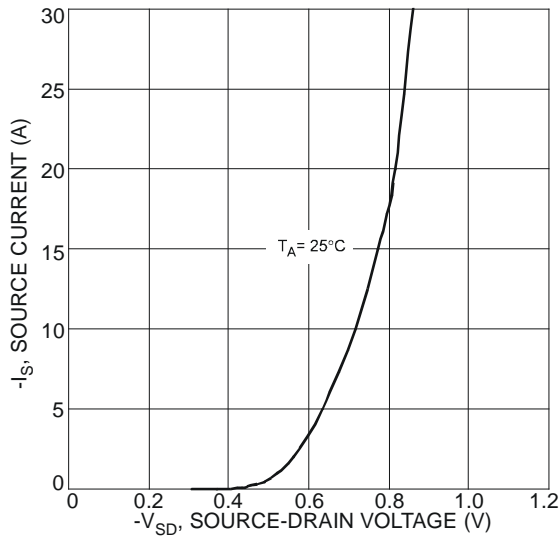


Fig. 9 Diode Forward Voltage vs. Current

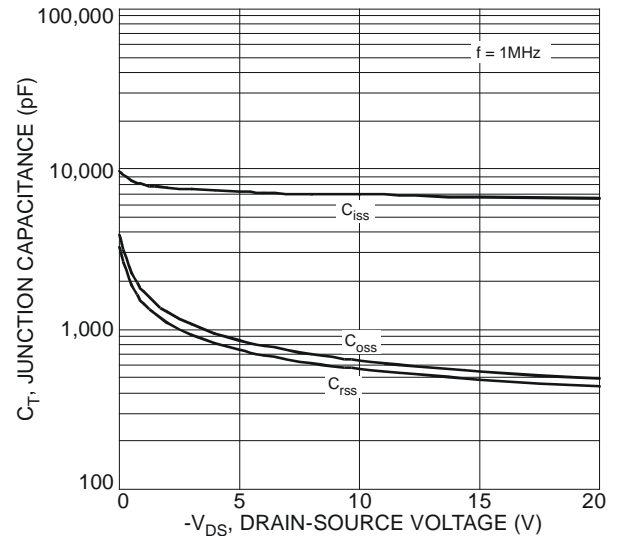


Fig. 10 Typical Junction Capacitance

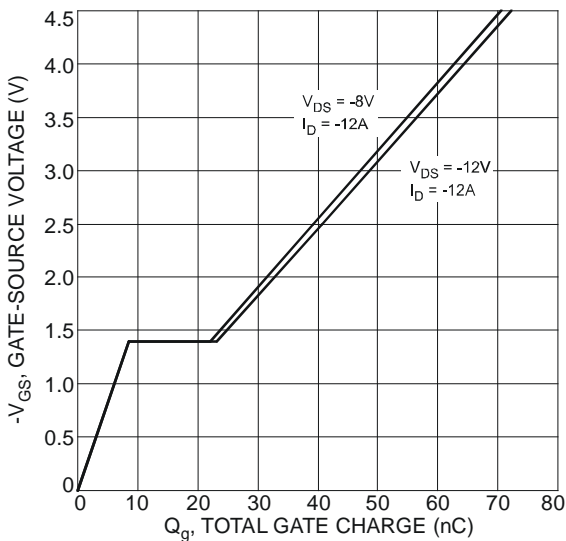


Fig. 11 Gate-Charge Characteristics

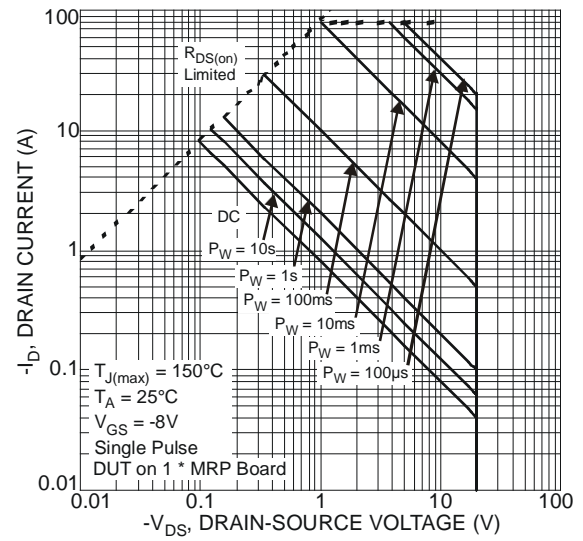


Fig. 12 SOA, Safe Operation Area

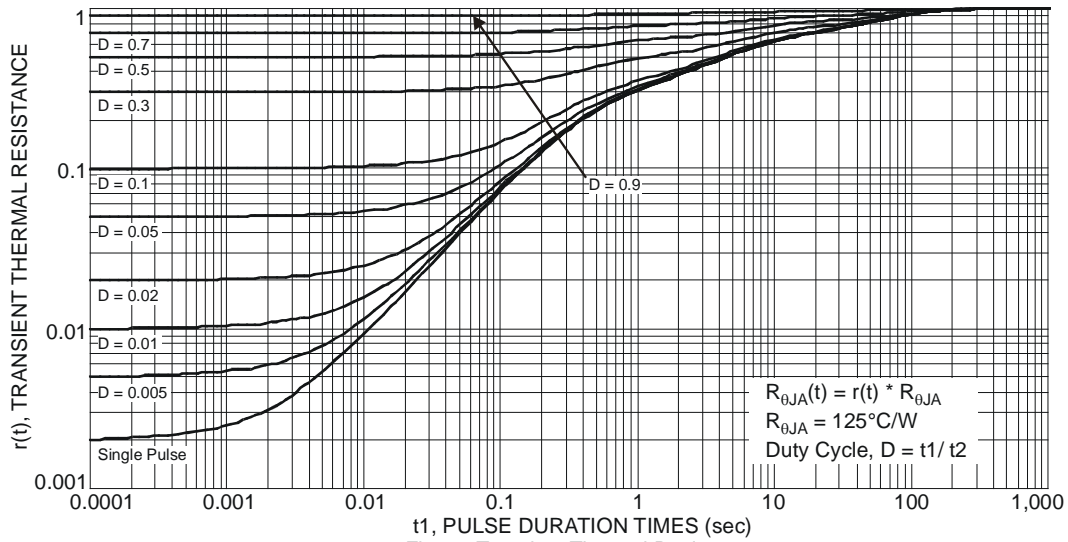
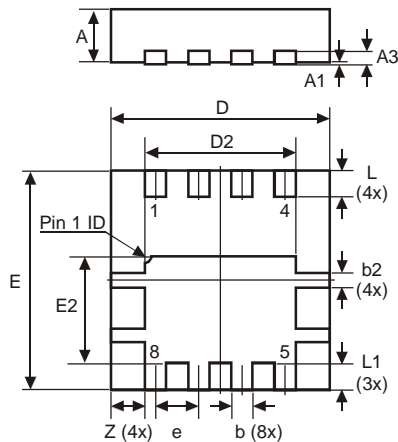


Fig. 13 Transient Thermal Resistance

## Package Outline Dimensions

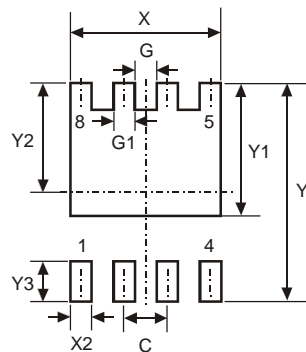
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



POWERDI3333-8			
Dim	Min	Max	Typ
D	3.25	3.35	3.30
E	3.25	3.35	3.30
D2	2.22	2.32	2.27
E2	1.56	1.66	1.61
A	0.75	0.85	0.80
A1	0	0.05	0.02
A3	—	—	0.203
b	0.27	0.37	0.32
b2	—	—	0.20
L	0.35	0.45	0.40
L1	—	—	0.39
e	—	—	0.65
Z	—	—	0.515
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.650
G	0.230
G1	0.420
Y	3.700
Y1	2.250
Y2	1.850
Y3	0.700
X	2.370
X2	0.420

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